FAIRCHILD

SEMICONDUCTOR

CD4069UBC Inverter Circuits

General Description

The CD4069UB consists of six inverter circuits and is manufactured using complementary MOS (CMOS) to achieve wide power supply operating range, low power consumption, high noise immunity, and symmetric controlled rise and fall times.

This device is intended for all general purpose inverter applications where the special characteristics of the MM74C901, MM74C907, and CD4049A Hex Inverter/Buffers are not required. In those applications requiring larger noise immunity the MM74C14 or MM74C914 Hex Schmitt Trigger is suggested.

All inputs are protected from damage due to static discharge by diode clamps to V_{DD} and $V_{\text{SS}}.$

Features

■ Wide supply voltage range: 3.0V to 15V

- \blacksquare High noise immunity: 0.45 V_{DD} typ.
- Low power TTL compatibility: Fan out of 2 driving 74L or 1 driving 74LS

October 1987

Revised April 2002

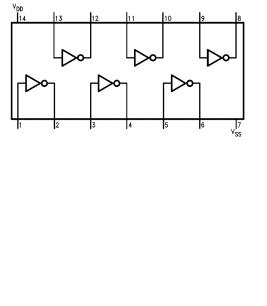
■ Equivalent to MM74C04

Ordering Code:

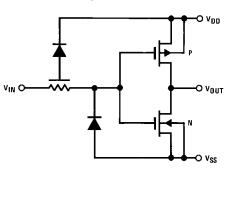
Order Number	Package Number	Package Description
CD4069UBCM	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
CD4069UBCSJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
02100002000		
CD4069UBCN	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
Dovice also available i	n Tana and Roal Specific	by appending suffix "X" to the ordering code

Device also available in Tape and Reel. Specify by appending suffix "X" to the ordering code.

Connection Diagram



Schematic Diagram



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Absolute Maximum Ratings(Note 1) (Note 2)

(11010 2)	
DC Supply Voltage (V _{DD})	-0.5V to $+18$ V _{DC}
Input Voltage (V _{IN})	–0.5V to V_DD +0.5 V_DC
Storage Temperature Range (T_S)	$-65^{\circ}C$ to $+150^{\circ}C$
Power Dissipation (P _D)	
Dual-In-Line	700 mW
Small Outline	500 mW
Lead Temperature (T _L)	
(Soldering, 10 seconds)	260°C

Recommended Operating Conditions (Note 2)

DC Supply Voltage (V_{DD}) Input Voltage (V_{IN}) 3V to $15V_{DC}$ 0V to V_{DD} V_{DC}

Note 2: $V_{SS} = 0V$ unless otherwise specified.

DC Electrical Characteristics (Note 3)

Symbol	Parameter	Conditions	-5	–55°C		+25°C			+125°C	
Symbol	Parameter	Conditions	Min	Max	Min	Тур	Max	Min	Max	Units
I _{DD}	Quiescent Device Current	$V_{DD} = 5V,$		0.25			0.25		7.5	
		$V_{IN} = V_{DD} \text{ or } V_{SS}$								
		$V_{DD} = 10V,$		0.5			0.5		15	μA
		$V_{IN} = V_{DD}$ or V_{SS}								μА
		$V_{DD} = 15V,$		1.0			1.0		30	
		$V_{IN} = V_{DD}$ or V_{SS}								
V _{OL}	LOW Level Output Voltage	I _O < 1 μA								
		$V_{DD} = 5V$		0.05		0	0.05		0.05	
		$V_{DD} = 10V$		0.05		0	0.05		0.05	V
		$V_{DD} = 15V$		0.05		0	0.05		0.05	
V _{OH}	HIGH Level Output Voltage	I _O < 1 μA								
		$V_{DD} = 5V$	4.95		4.95	5		4.95		
		$V_{DD} = 10V$	9.95		9.95	10		9.95		V
		$V_{DD} = 15V$	14.95		14.95	15		14.95		
VIL	LOW Level Input Voltage	I _O < 1 μA								
		$V_{DD}=5V,\ V_O=4.5V$		1.0			1.0		1.0	
		$V_{DD} = 10V, V_O = 9V$		2.0			2.0		2.0	V
		$V_{DD} = 15V, V_{O} = 13.5V$		3.0			3.0		3.0	
VIH	HIGH Level Input Voltage	I _O < 1 μA								
		$V_{DD} = 5V, V_{O} = 0.5V$	4.0		4.0			4.0		
		$V_{DD} = 10V, V_{O} = 1V$	8.0		8.0			8.0		V
		$V_{DD} = 15V, V_{O} = 1.5V$	12.0		12.0			12.0		
I _{OL}	LOW Level Output Current	$V_{DD} = 5V, V_{O} = 0.4V$	0.64		0.51	0.88		0.36		
	(Note 4)	$V_{DD} = 10V, V_{O} = 0.5V$	1.6		1.3	2.25		0.9		mA
		$V_{DD} = 15V, V_{O} = 1.5V$	4.2		3.4	8.8		2.4		
I _{OH}	HIGH Level Output Current	$V_{DD} = 5V, V_{O} = 4.6V$	-0.64		-0.51	-0.88		-0.36		
	(Note 4)	$V_{DD} = 10V, V_{O} = 9.5V$	-1.6		-1.3	-2.25		-0.9		mA
		$V_{DD} = 15V, V_{O} = 13.5V$	-4.2		-3.4	-8.8		-2.4		
I _{IN}	Input Current	$V_{DD} = 15V, V_{IN} = 0V$		-0.1		-10 ⁻⁵	-0.1		-1.0	
		$V_{DD} = 15V, V_{IN} = 15V$		0.1		10 ⁻⁵	0.1		1.0	μA

Note 3: $V_{SS} = 0V$ unless otherwise specified.

Note 4: ${\rm I}_{\rm OH}$ and ${\rm I}_{\rm OL}$ are tested one output at a time.

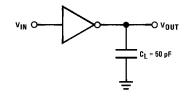
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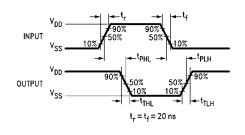
$T_A = 25^{\circ}C$, $C_L = 50$ pF, $R_L = 200$ k Ω , t_r and $t_f \le 20$ ns, unless otherwise specified							
Symbol	Parameter	Conditions	Min	Тур	Max	Units	
t _{PHL} or t _{PLH}	Propagation Delay Time from	$V_{DD} = 5V$		50	90		
	Input to Output	$V_{DD} = 10V$		30	60	ns	
		$V_{DD} = 15V$		25	50		
t _{THL} or t _{TLH}	Transition Time	$V_{DD} = 5V$		80	150		
		$V_{DD} = 10V$		50	100	ns	
		$V_{DD} = 15V$		40	80		
C _{IN}	Average Input Capacitance	Any Gate		6	15	pF	
C _{PD}	Power Dissipation Capacitance	Any Gate (Note 6)		12		pF	

Note 5: AC Parameters are guaranteed by DC correlated testing.

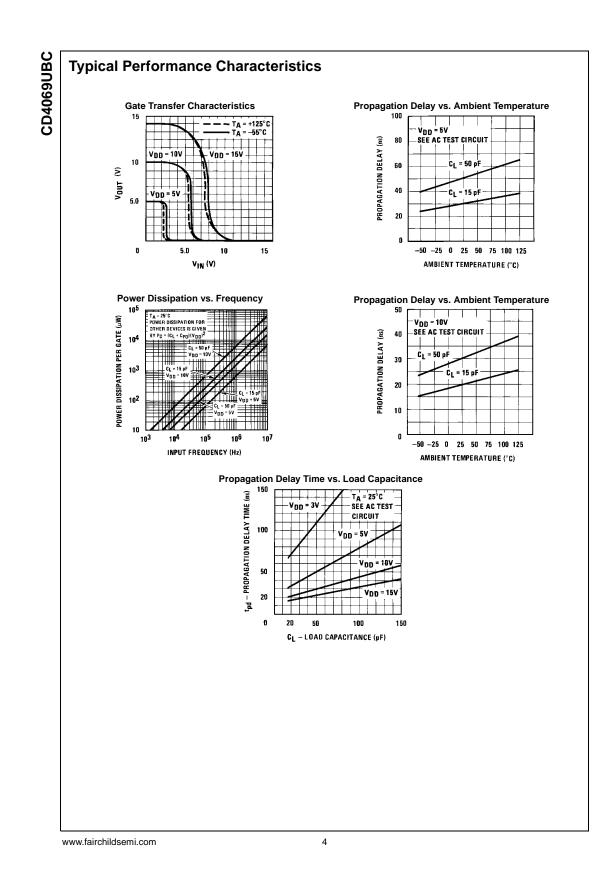
Note 6: C_{PD} determines the no load AC power consumption of any CMOS device. For complete explanation, see Family Characteristics application note— AN-90.

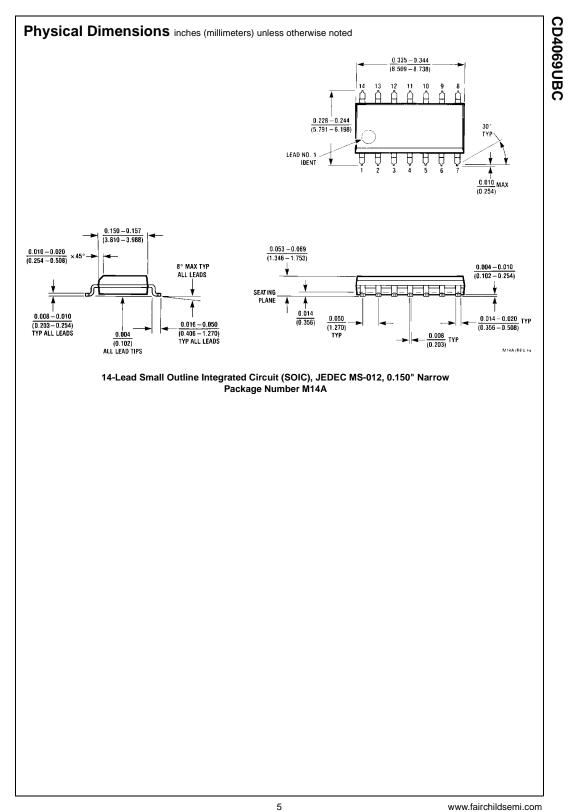
AC Test Circuits and Switching Time Waveforms

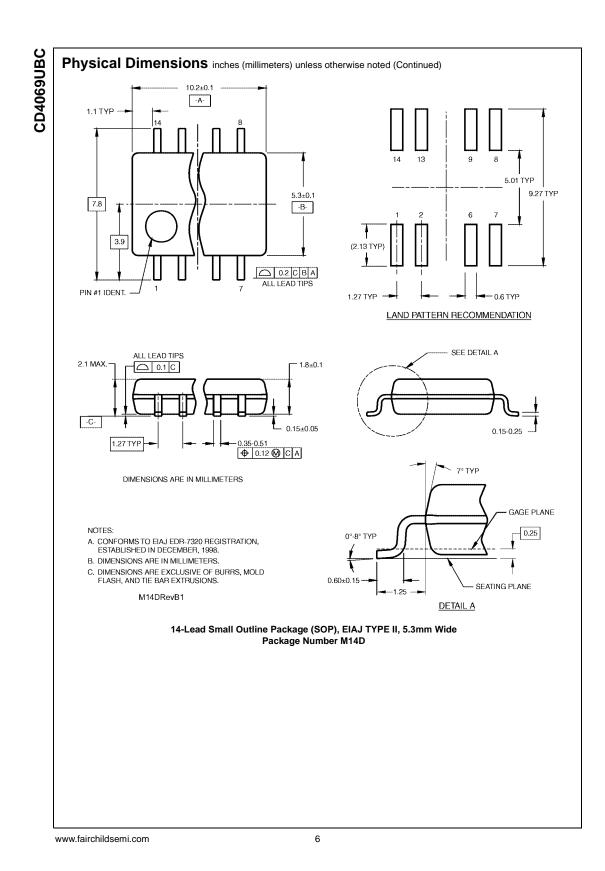




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